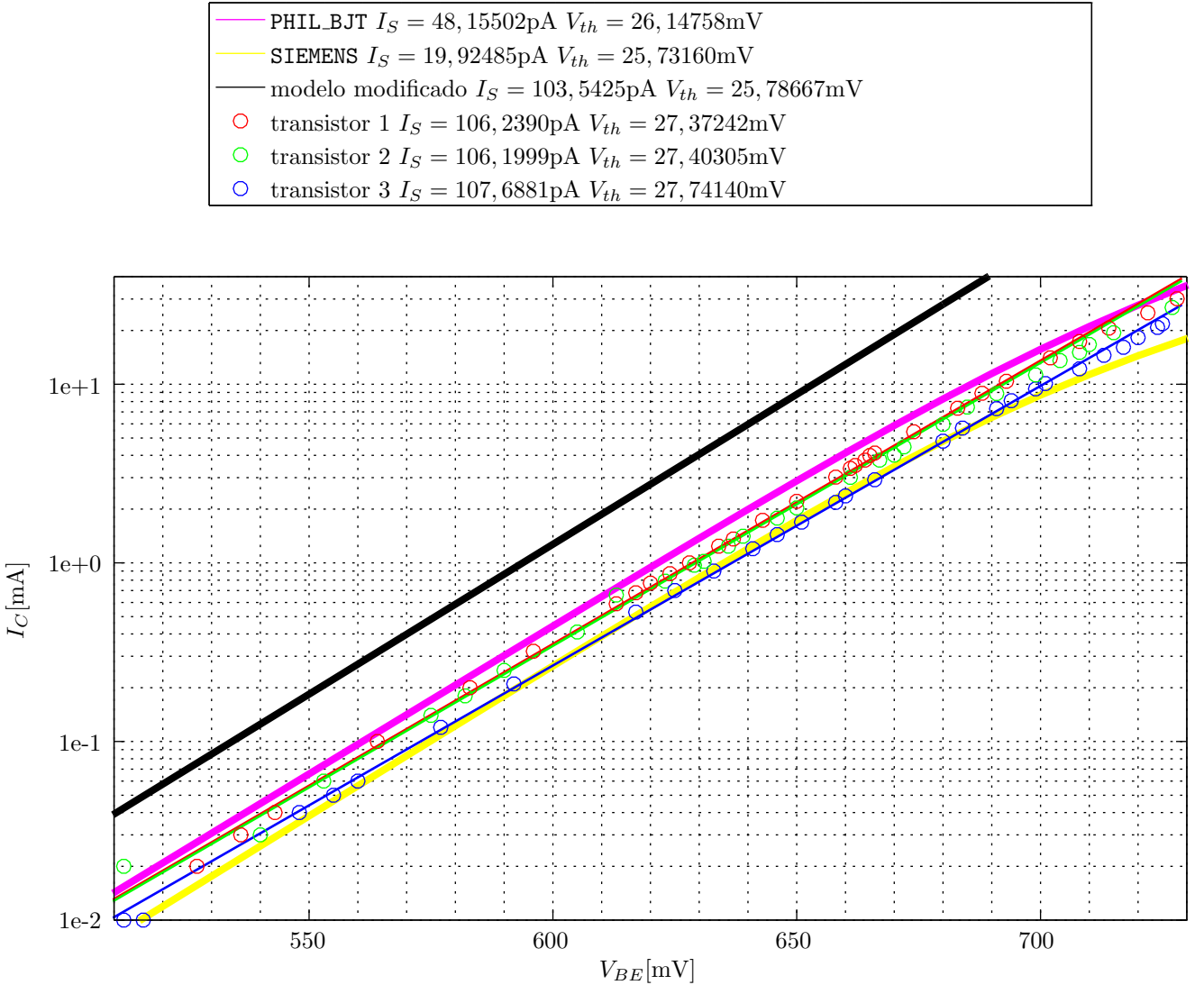
PHIL_BJT $I_S = 48,15502\text{pA}$ $V_{th} = 26,14758\text{mV}$
SIEMENS $I_S = 19,92485\text{pA}$ $V_{th} = 25,73160\text{mV}$
modelo modificado $I_S = 103,5425\text{pA}$ $V_{th} = 25,78667\text{mV}$
transistor 1 $I_S = 106,2390\text{pA}$ $V_{th} = 27,37242\text{mV}$
transistor 2 $I_S = 106,1999\text{pA}$ $V_{th} = 27,40305\text{mV}$
transistor 3 $I_S = 107,6881\text{pA}$ $V_{th} = 27,74140\text{mV}$
1e+1
1e+0
1e-1
1e-2
I_C[mA]
550
600
650
700
V_{BE}[mV]